

SILICON POWER TRANSISTOR

2SC2335

NPN SILICON TRIPLE DIFFUSED TRANSISTOR FOR HIGH-SPEED HIGH-VOLTAGE SWITCHING

The 2SC2335 is a mold power transistor developed for high-speed high-voltage switching, and is ideal for use as a driver in devices such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

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FEATURES

- Low collector saturation voltage: VcE(sat) = 1.0 V MAX. @ Ic = 3.0 A
- Fast switching speed: $t_f = 1.0 \mu s$ MAX. @Ic = 3.0 A
- Wide base reverse-bias SOA: Vcex(sus)1 = 450 V MIN. @ Ic = 3.0 A

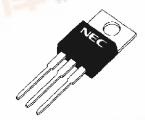
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------------------|--|-------------|------|
| Collector to base voltage | Vсво | | 500 | V |
| Collector to emitter voltage | Vceo | | 400 | V |
| Emitter to base voltage | VEBO | | 7.0 | V |
| Collector current (DC) | Ic(DC) | | 7.0 | Α |
| Collector current (pulse) | IC(pulse) | PW \leq 300 μ s, duty cycle \leq 10% | 15 | Α |
| Base current (DC) | I _{B(DC)} | | 3.5 | Α |
| Total power dissipation | Рт | Tc = 25°C | 40 | W |
| | - 47 | T _A = 25°C | 1.5 | W |
| Junction temperature | Tj | WW.DLS | 150 | °C |
| Storage temperature | Tstg | ** | -55 to +150 | °C |

ORDERING INFORMATION

| Part No. | Package |
|----------|----------|
| 2SC2335 | TO-220AB |

(TO-220AB)







ELECTRICAL CHARACTERISTICS (TA = 25°C)

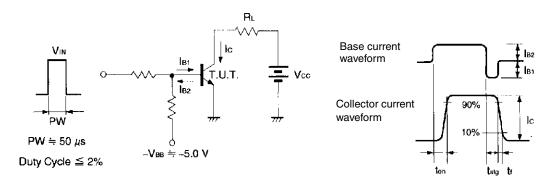
| Parameter | Symbol | Conditions | MIN. | TYP. | MAX. | Unit |
|------------------------------|----------------------|---|------|------|------|------|
| Collector to emitter voltage | VCEO(SUS) | Ic = 3.0 A, I _{B1} = 0.6 A, L = 1 mH | 400 | | | V |
| Collector to emitter voltage | VCEX(SUS)1 | Ic = 3.0 A, I _{B1} = $-I_{B2}$ = 0.6 A, V _{BE(OFF)} = -5.0 V, L = 180 μ H, clamped | 450 | | | V |
| Collector to emitter voltage | VCEX(SUS)2 | Ic = 6.0 A, I _{B1} = 2.0 A, $-I_{B2}$ = 0.6 A, V _{BE(OFF)} = -5.0 V, L = 180 μ H, clamped | | | | V |
| Collector cutoff current | Ісво | V _{CB} = 400 V, I _E = 0 A | | | 10 | μΑ |
| Collector cutoff current | ICER | $V_{\text{CE}} = 400 \text{ V}, \text{ Rbe} = 51 \ \Omega, \text{ Ta} = 125 ^{\circ}\text{C}$ | | | 1.0 | mA |
| Collector cutoff current | ICEX1 | $V_{CE} = 400 \text{ V}, V_{BE(OFF)} = -1.5 \text{ V}$ | | | 10 | μΑ |
| Collector cutoff current | ICEX2 | $V_{CE} = 400 \text{ V}, V_{BE(OFF)} = -1.5 \text{ V},$ $T_A = 125^{\circ}\text{C}$ | | | 1.0 | mA |
| Emitter cutoff current | І ЕВО | V _{EB} = 5.0 V, I _C = 0 A | | | 10 | μΑ |
| DC current gain | h _{FE1} | $V_{CE} = 5.0 \text{ V, } I_{C} = 0.1 \text{ A}^{Note}$ | 20 | | 80 | |
| DC current gain | h _{FE2} | $V_{CE} = 5.0 \text{ V, Ic} = 1.0 \text{ A}^{\text{Note}}$ | 20 | | 80 | |
| DC current gain | h _{FE3} | $V_{CE} = 5.0 \text{ V}, I_{C} = 3.0 \text{ A}^{\text{Note}}$ | 10 | | | |
| Collector saturation voltage | V _{CE(sat)} | $I_{C} = 3.0 \text{ A}, I_{B} = 0.6 \text{ A}^{\text{Note}}$ | | | 1.0 | V |
| Base saturation voltage | V _{BE(sat)} | $I_{C} = 3.0 \text{ A}, I_{B} = 0.6 \text{ A}^{\text{Note}}$ | | | 1.2 | V |
| Turn-on time | ton | Ic = 3.0 A, R_L = 50 Ω, | | | 1.0 | μs |
| Storage time | tstg | $I_{B1} = -I_{B2} = 0.6 \text{ A}, \text{ Vcc} \cong 150 \text{ V}$ | | | 2.5 | μs |
| Fall time | t f | Refer to the test circuit. | | | 1.0 | μs |

Note Pulse test PW \leq 350 μ s, duty cycle \leq 2%

hfe CLASSIFICATION

| Marking | М | L | К | |
|------------------|----------|----------|----------|--|
| h _{FE2} | 20 to 40 | 30 to 60 | 40 to 80 | |

SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

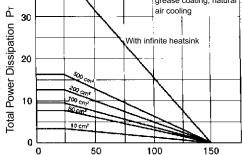


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TYPICAL CHARACTERISTICS (TA = 25°C)

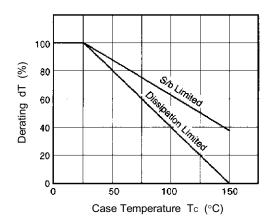


TOTAL POWER DISSIPATION vs. AMBIENT

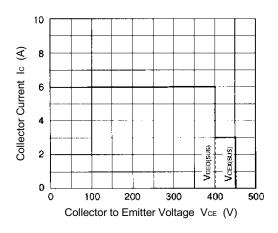


DERATING CURVE OF SAFE OPERATING AREAS

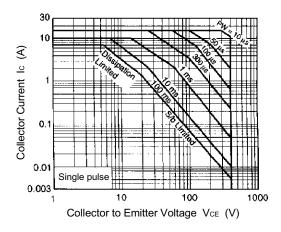
Ambient Temperature TA (°C)



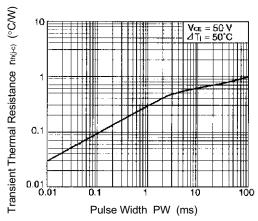
REVERSE BIAS SAFE OPERATING AREAS



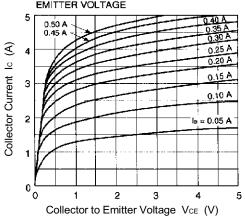
FORWARD BIAS SAFE OPERATING AREAS



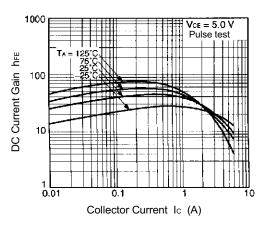
TRANSIENT THERMAL RESISTANCE



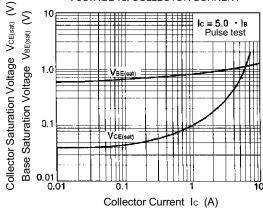




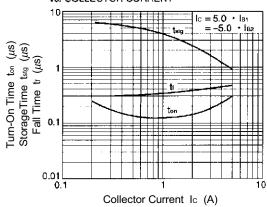
DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT

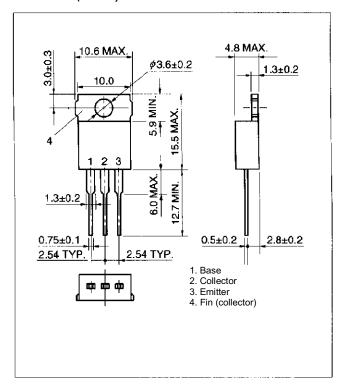


TURN ON TIME, STORAGE TIME AND FALL TIME vs. COLLECTOR CURRENT



PACKAGE DRAWING (UNIT: mm)

TO-220AB (MP-25)



(Note)

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